

A METHOD OF IMPROVING ADHESION OF CAP OXIDE TO NANOPOROUS SILICA FOR INTEGRATED CIRCUIT FABRICATION

ABSTRACT OF THE DISCLOSURE

5        A method of improving adhesion of a cap oxide to nanoporous silica for  
integrated circuit fabrication. In one embodiment, the method comprises several  
steps. The first step is to receive a wafer in a deposition chamber. Then a porous  
layer of material is deposited on the wafer. Next, a portion of the porous layer is  
densified in order to make it more compatible for adhesion to a cap layer. Finally, a  
10      cap layer is deposited onto the porous layer.

TOP SECRET - SOURCE CODE